

V_{RSM} V_{RRM} V	$I_D (T_h = 80^\circ\text{C})$	
	51 A	72 A
800	SK 50 B 08	SK 70 D 08
1200	SK 50 B 12	SK 70 D 12
1600	SK 50 B 16	SK 70 D 16

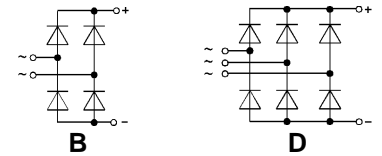
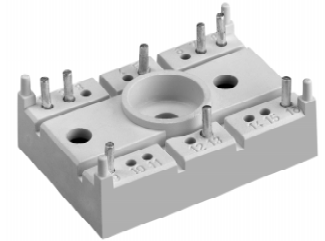
SEMITOP® 2

Bridge Rectifier

SK 50 B SK 70 D

Preliminary Data

Symbol	Conditions	SK 50 B	SK 70 D	Units
I_D	$T_h = 80^\circ\text{C}$	51	72	A
I_{FSM} i^2t	$T_{vj} = 25^\circ\text{C}; 10\text{ ms}$	-		A
	$T_{vj} = 125^\circ\text{C}; 10\text{ ms}$	350		A
	$T_{vj} = 25^\circ\text{C}; 8,3...10\text{ ms}$	-		A ² s
	$T_{vj} = 125^\circ\text{C}; 8,3...10\text{ ms}$	-		A ² s
V_F	$T_{vj} = 125^\circ\text{C}; (I_T = 25\text{ A}); \text{max.}$	1,1		V
$V_{(T0)}$	$T_{vj} = 125^\circ\text{C}$	0,8		V
r_T	$T_{vj} = 125^\circ\text{C}$	13		mΩ
I_{RD}	$T_{vj} = 25^\circ\text{C}; V_{RD} = V_{RRM}$	-		mA
R_{thjh}	per diode	1,7	1,7	K/W
	per module	0,43	0,28	K/W
T_{vj}		- 40 ... + 125		°C
T_{st}		- 40 ... + 125		°C
T_{solder}	terminals, 10 s	260		°C
V_{isol}	a.c. 50 Hz; r.m.s. 1 s/1 min	3000 / 2500		V
M_1	case to heatsink	2,0		Nm
	SI units	17,6		lb.in.
w	US units	-		g
Case		T 6		



Features

- Compact Design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Up to 1600V reverse voltage
- High surge currents
- Glass passivated diode chips

Typical Applications

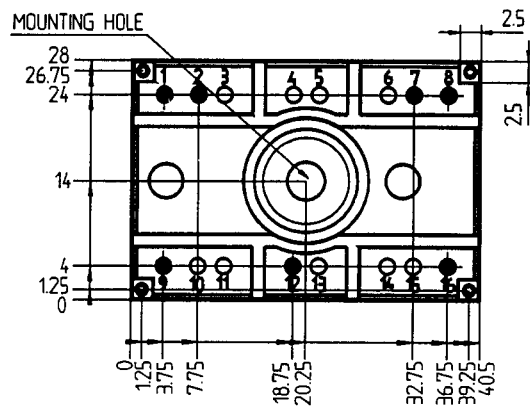
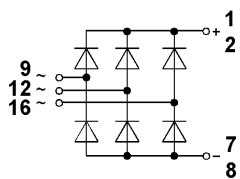
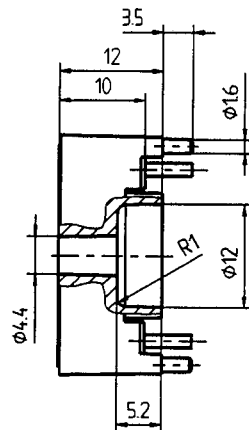
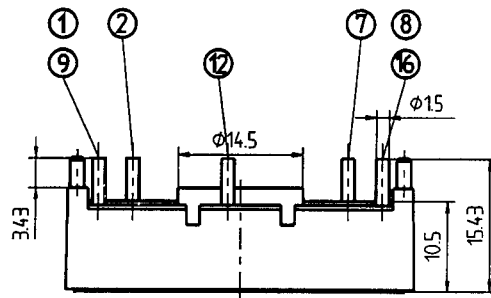
- Input rectifier for power supplies
- Rectifier

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SK 70 D

SK 95 D

Case T 7

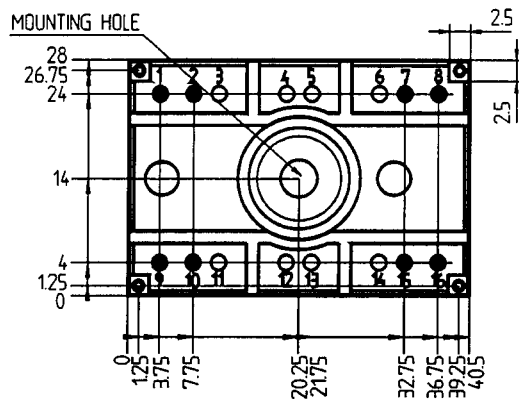
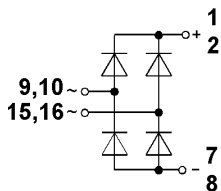
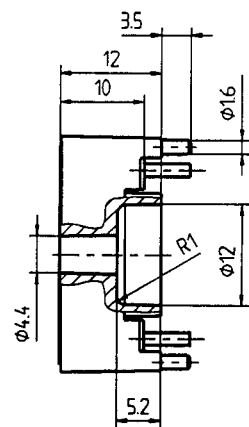
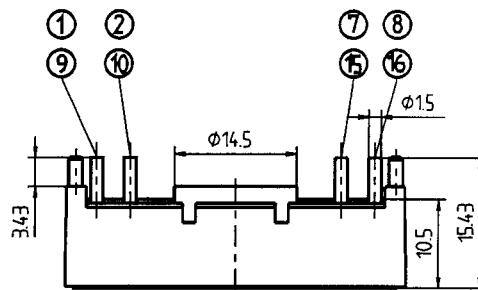


SEMITOP® 2

SK 50 B

SK 75 B

Case T 6



Dimensions in mm